

AMENDMENT TO THE CLAIMS

1. (currently amended) A method of making an electrically programmable memory element, comprising the steps of:

providing a first conductive material;

removing a portion of said first conductive material;

replacing at least a portion of said removed first conductive material with a second conductive material, said second conductive material having a resistivity which is ~~different from~~ greater than the resistivity of said ~~removed~~ first conductive material; and

introducing a programmable resistance material proximate to said second conductive material and distant from said first conductive material.

Claims 2-5 (canceled)

6. (original) The method of claim 1, wherein said programmable resistance material is a phase change material.

7. (original) The method of claim 1, wherein said programmable resistance material includes a chalcogen element.

Claims 8, 9 (canceled)

10. (new) The method of claim 1, wherein said first conductive material is doped differently from said second conductive material.